

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
M122-1784

SERIAL NO.

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Luan Tran et al.

FILING DATE

GROUP

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,045,899	09/03/91	Arimoto			
	AB	5,107,459	04/21/92	Chu et al.			
	AC	5,350,706	09/27/94	McElroy et al.			
	AD	5,469,383	11/21/95	McElroy et al.			
	AE	5,537,347	07/16/96	Shiratake et al.			
	AF	5,508,541	04/16/96	Hieda et al.			
	AG	5,383,151	01/17/95	Onishi et al.			
	AH	5,726,092	03/10/98	Mathews et al.			
	AI	5,595,928	01/21/97	Lu et al.			
	AJ	5,747,844	05/05/98	Aoki et al.			
	AK	5,665,623	09/09/97	Liang et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL	JP 03205868	09/09/91	Japan			Abs.	
	AM							
	AN							
	AO							
	AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR	A. Chatterjee et al., "A Shallow Trench Isolation Study for 0.25/0.18 μ m CMOS Technologies and Beyond",
		IEEE, 1996 Symposium on VLSI Technology Digest of Technical Papers, pp. 156-57 (1996).
	AS	M. Aoki et al., "Fully Self-Aligned 6F ² Cell Technology for Low Cost 1Gb DRAM", IEEE
		1996 Symposium on VLSI Technology Digest of Technical Papers, pp. 22-23 (1996).
	AT	J.S. KIM et al., "A Triple Level Metallization Technique for Gigabit Scaled DRAMS", VMIC CONFERENCE, Technology
		Development, Memory Device Business, Samsung Electronic Co., pp. 28-33 (June 18-20, 1996).

EXAMINER

DATE CONSIDERED

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				FILING DATE	GROUP		
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,637,528	06/10/97	Higashitani et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
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							Yes No
	AL						
	AM						
	AN						
	AO						
	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		B. KEETH, "A Novel Architecture for Advanced High Density Dynamic Random Access Memories", A Thesis for M.S. E.E., University of Idaho pp. 1-62 (i-vi); (May 1996).				
	AS		T. Hamamoto et al., "NAND-Structured Trench Capacitor Cell Technologies for 256 Mb DRAM and Beyond", IEICE Transactions On Electronics, pp. 789-796, 1995.				
	AT		M. Noguchi et al., "0.29- μm^2 Trench Cell Technologies for 1G-bit DRAMs with Open/Folded-Bit-Line Layout and Selective Growth Technique", 1995 Symposium on VLSI Technology Digest of Technical Papers, pp. 137-138.				
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	AA						
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AM						
	AN						
	AO						
	AP						
	AQ						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		V. Mathews et al., <i>Dry O₂ High Presure Field Oxidation for 0.25 μm Isolation Technology</i> .				
			SSDM '95 - Device and Process Technology, 2 pages.				
	AS						
	AT						
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